## **TOSHIBA**

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

# 2SK2989

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance  $: R_{DS} (ON) = 120 \text{ m}\Omega (typ.)$
- High forward transfer admittance  $: |Y_{fs}| = 2.6 \text{ S (typ.)}$
- Low leakage current  $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 50 \ V)$
- Enhancement-mode :  $V_{th} = 0.8 \sim 2.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{I}_{D} = 1 \text{ mA})$

#### Maximum Ratings (Ta = 25°C)

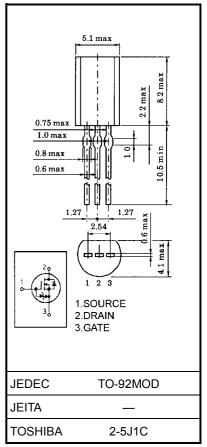
Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	50	V	
Drain-gate voltage (R	<sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	50	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	5	А	
	Pulse (Note 1)	I <sub>DP</sub>	15	~	
Drain power dissipation	ı	PD	0.9	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

#### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch−a)</sub>	138	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device. Please handle with caution.



Weight: 0.36 g (typ.)

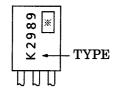
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V		_	±10	μA
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V		_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	50	_	-	V
Gate threshold v	voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	0.8		2.0	V
Drain-source ON resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 4 V, I <sub>D</sub> = 1.3 A		240	330	mΩ
			V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A		120	150	11152
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A	1.3	2.6	—	S
Input capacitance	ce	C <sub>iss</sub>			145	-	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		25	-	pF
Output capacitance		C <sub>oss</sub>			75	_	
Switching time	Rise time	tr	$V_{GS} \xrightarrow{10V}_{0V} \prod_{\substack{ID = 2.5A \\ 0V \\ 0V \\ C}} V_{OUT} \xrightarrow{R_L = 10\Omega} V_{OUT}$	_	16	_	
	Turn-on time	t <sub>on</sub>		_	23	_	
	Fall time	t <sub>f</sub>		_	27	_	- ns
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , t <sub>w</sub> =10µs	_	110	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	6.5	_	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 40 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ A}$	—	5	_	nC
Gate-drain ("miller") Charge		Q <sub>gd</sub>	]		1.5	_	

#### Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	5	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	-	_	_	15	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	_	-1.5	V

### Marking



- % Lot Number
  - Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)

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